

# 2N2723

CASE 20-03, STYLE 8  
TO-72 (TO-206AF)

**DARLINGTON TRANSISTOR**

**NPN SILICON**

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage (Base 1 and Base 2 open)	V <sub>CE2O</sub>	60	Vdc
Collector-Base Voltage	V <sub>CB1</sub>	80	Vdc
Emitter-Base Voltage	V <sub>E2B1</sub>	12	Vdc
Collector Current — Continuous	I <sub>C</sub>	40	Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	0.5 2.9	Watt mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.8 10.5	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage(1) (I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 0)	V <sub>(BR)CE2O</sub>	60	—	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E2</sub> = 0)	V <sub>(BR)CB1O</sub>	80	—	Vdc
Emitter-Base Breakdown Voltage (I <sub>E2</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)E2B1O</sub>	12	—	Vdc
Collector Cutoff Current (V <sub>CB1</sub> = 60 Vdc, I <sub>E</sub> = 0) (V <sub>CB1</sub> = 60 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>CB1O</sub>	—	0.01 10	μAdc
Emitter Cutoff Current (V <sub>B1E2</sub> = 10 Vdc, I <sub>C</sub> = 0)	I <sub>E2B1O</sub>	—	10	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (I <sub>C</sub> = 10 mAdc, V <sub>CE2</sub> = 5.0 Vdc, I <sub>B2</sub> = 0)	h <sub>FE</sub>	2000	10,000	—
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)	V <sub>CE2(sat)</sub>	—	1.0	Vdc
Base-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)	V <sub>BE2(sat)</sub>	—	1.7	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Output Capacitance (V <sub>CB1</sub> = 10 Vdc, I <sub>E2</sub> = 0, f = 140 kHz)	C <sub>ob1o</sub>	—	10	pF
Small-Signal Current Gain (I <sub>C</sub> = 10 mAdc, V <sub>CE2</sub> = 5.0 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	1500	15,000	—
Current Gain — Bandwidth Product (Each Unit) (I <sub>C</sub> = 10 mAdc, V <sub>CE1</sub> or V <sub>CE2</sub> = 10 Vdc, f = 20 MHz)	h <sub>fe</sub> f	5.0	—	—
Noise Figure (Input Stage Only) (I <sub>C</sub> = 50 μAdc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 3.0 kohms, f = 1.0 kHz, BW = 100 Hz)	NF	—	10	dB

(1) Pulse Test: Pulse Width ≤ 12 ms, Duty Cycle ≤ 2.0%.